Designer's™ Data Sheet

Complementary NPN-PNP Silicon Power Bipolar Transistor

The MJ3281A and MJ1302A are PowerBase power transistors for high power audio, disk head positioners and other linear applications.

- Designed for 100 W Audio Frequency
- Gain Complementary:
 - Gain Linearity from 100 mA to 7 A
 - High Gain 60 to 175
 - h_{FE} = 45 (Min) @ I_C = 8 A
- Low Harmonic Distortion
- High Safe Operation Area 1 A/100 V @ 1 sec
- High f_T 30 MHz Typical

MJ3281A* PNP MJ1302A*

*Motorola Preferred Device

15 AMPERE
COMPLEMENTARY
SILICON POWER
TRANSISTORS
200 VOLTS
250 WATTS



CASE 1-07 TO-204AA (TO-3)

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating		Symbol	Value	Unit
Collector–Emitter Voltage		VCEO	200	Vdc
Collector-Base Voltage		VCBO	200	Vdc
Emitter-Base Voltage		VEBO	W.OZSC.	Vdc
Collector–Emitter Voltage — 1.5 V		VCEX	200	Vdc
Collector Current — Continuous — Peak (1)	P.	IC	15 25	Adc
Base Current — Continuous		ΙΒ	1.5	Adc
Total Power Dissipation @ T _C = 25°C Derate Above 25°C		PD	250 1.43	Watts W/°C
Operating and Storage Junction Temperature Range		TJ, T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R ₀ JC	0.7	°C/W

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle <10%.

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

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eferred devices are Motorola recommended choices for future use and best overall value.



MJ3281A MJ1302A

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•	
Collector–Emitter Sustaining Voltage (I _C = 100 mAdc, I _B = 0)	V _{CEO(sus)}	200	_	_	Vdc
Emitter–Base Voltage ($I_E = 100 \mu Adc$, $I_C = 0$)	VEBO	7	_	_	Vdc
Collector Cutoff Current (V _{CB} = 200 Vdc, I _E = 0)	ICBO	_	_	50	μAdc
Emitter Cutoff Current (VEB = 5 Vdc, IC = 0)	IEBO	_	_	5	μAdc
Emitter Cutoff Current (VEB = 7 Vdc, IC = 0)	IEBO	_	_	25	μAdc
SECOND BREAKDOWN			•	•	
Second Breakdown Collector with Base Forward Biased (VCE = 50 Vdc, t = 1 s (non–repetitive) (VCE = 100 Vdc, t = 1 s (non–repetitive)	I _{S/b}	4 1	_	_	Adc
ON CHARACTERISTICS			•	•	
DC Current Gain $(IC = 100 \text{ mAdc}, V_{CE} = 5 \text{ Vdc})$ $(IC = 1 \text{ Adc}, V_{CE} = 5 \text{ Vdc})$ $(IC = 3 \text{ Adc}, V_{CE} = 5 \text{ Vdc})$ $(IC = 5 \text{ Adc}, V_{CE} = 5 \text{ Vdc})$ $(IC = 7 \text{ Adc}, V_{CE} = 5 \text{ Vdc})$ $(IC = 8 \text{ Adc}, V_{CE} = 5 \text{ Vdc})$ $(IC = 15 \text{ Adc}, V_{CE} = 5 \text{ Vdc})$	hFE	60 60 60 60 60 45 12	125 — — — 115 — 35	175 175 175 175 175 175 —	
Collector–Emitter Saturation Voltage (I _C = 10 Adc, I _B = 1 Adc)	VCE(sat)	_	_	3	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I _C = 1 Adc, V _{CE} = 5 Vdc, f _{test} = 1 MHz)	fT	_	30	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz)	C _{ob}	_		600	pF

⁽¹⁾ Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2%.

M. 15: 15 T. T. 11 D. 15: 1

TYPICAL CHARACTERISTICS

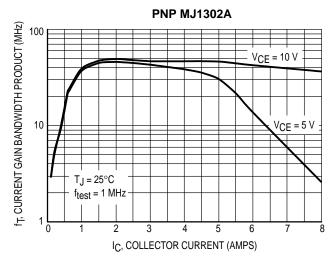


Figure 1. Current-Gain — Bandwidth Product

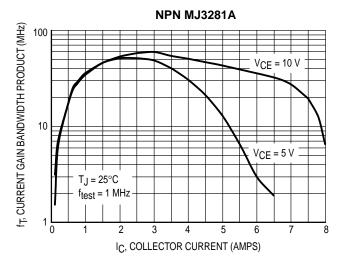


Figure 2. Current-Gain — Bandwidth Product

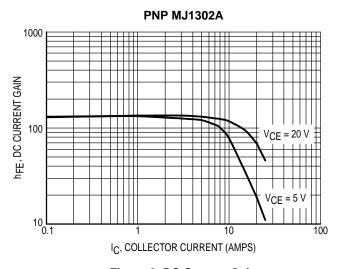


Figure 3. DC Current Gain

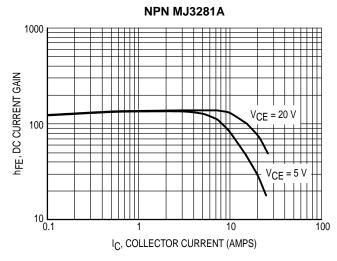


Figure 4. DC Current Gain

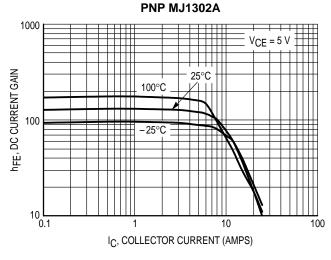


Figure 5. DC Current Gain, VCE = 5 V

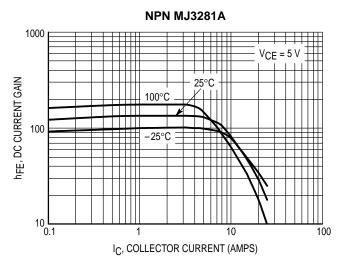


Figure 6. DC Current Gain, VCE = 5 V

TYPICAL CHARACTERISTICS

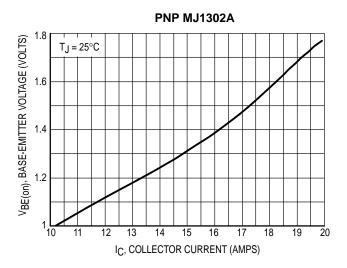


Figure 7. Typical Base-Emitter Voltage

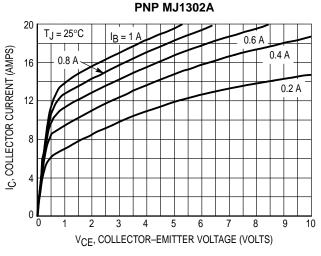


Figure 9. Typical Output Characteristics

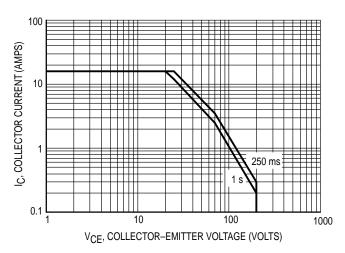


Figure 11. Forward Bias Safe Operating Area (FBSOA)

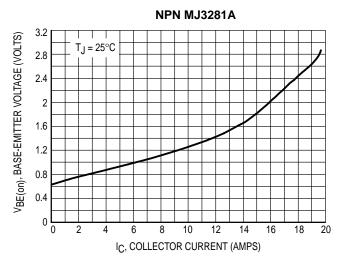


Figure 8. Typical Base-Emitter Voltage

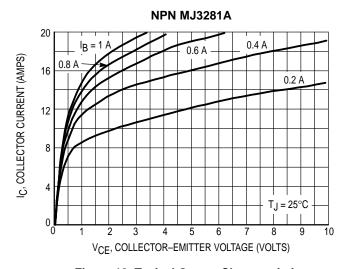
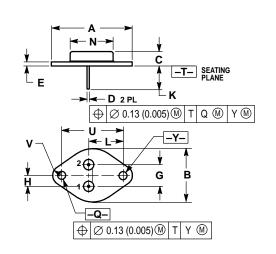


Figure 10. Typical Output Characteristics

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 11 is based on $T_{J(pk)} = 200^{\circ}C$; T_{C} is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37 REF		
В		1.050		26.67	
С	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
Е	0.055	0.070	1.40	1.77	
G	0.430	BSC	10.92 BSC		
Н	0.215	BSC	5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665 BSC		16.89 BSC		
N		0.830		21.08	
Q	0.151	0.165	3.84	4.19	
U	1.187	BSC	30.15 BSC		
٧	0.131	0.188	3.33	4.77	

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

CASE 1-07 TO-204AA (TO-3) ISSUE Z

MJ3281A MJ1302A

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